

# PSMN4R0-30YL

## N-channel TrenchMOS logic level FET

Rev. 01 — 10 September 2008

Preliminary data sheet

## 1. Product profile

### 1.1 General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product is designed and qualified for use in industrial and communications applications.

### 1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for logic level gate drive sources

### 1.3 Applications

- Class-D amplifiers
- DC-to-DC converters
- Motor control
- Server power supplies

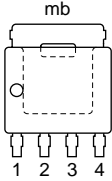
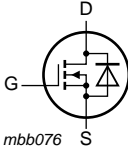
### 1.4 Quick reference data

Table 1. Quick reference

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{DS}$	drain-source voltage	$T_j \geq 25\text{ °C}$ ; $T_j \leq 150\text{ °C}$	-	-	30	V
$I_D$	drain current	$T_{mb} = 25\text{ °C}$ ; $V_{GS} = 10\text{ V}$ ; see <a href="#">Figure 1</a>	-	-	99	A
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ °C}$ ; see <a href="#">Figure 2</a>	-	-	69	W
<b>Dynamic characteristics</b>						
$Q_{GD}$	gate-drain charge	$V_{GS} = 4.5\text{ V}$ ; $I_D = 10\text{ A}$ ; $V_{DS} = 12\text{ V}$ ; see <a href="#">Figure 14</a> ; see <a href="#">Figure 15</a>	-	4.3	-	nC
<b>Static characteristics</b>						
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}$ ; $I_D = 15\text{ A}$ ; $T_j = 25\text{ °C}$ ; see <a href="#">Figure 12</a>	-	2.69	4	m $\Omega$

## 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	 <p>SOT669 (LFPACK)</p>	 <p>mbb076</p>
2	S	source		
3	S	source		
4	G	gate		
mb	D	mounting base; connected to drain		

## 3. Ordering information

Table 3. Ordering information

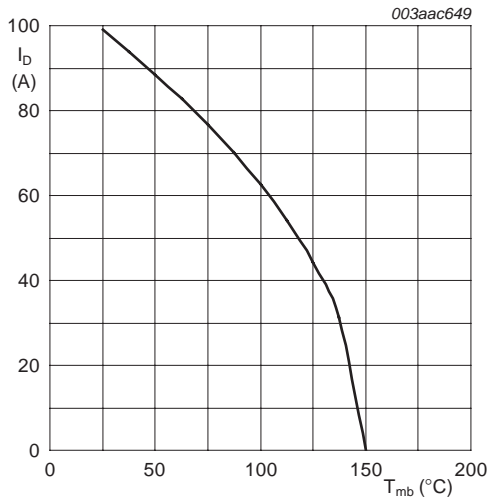
Type number	Package		Description	Version
	Name			
PSMN4R0-30YL	LFPACK		Plastic single-ended surface-mounted package (LFPACK); 4 leads	SOT669

## 4. Limiting values

Table 4. Limiting values

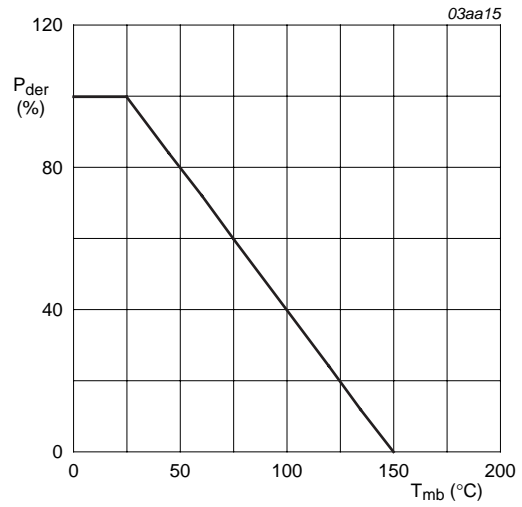
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage	$T_j \geq 25\text{ °C}; T_j \leq 150\text{ °C}$	-	30	V
$V_{DGR}$	drain-gate voltage	$T_j \geq 25\text{ °C}; T_j \leq 150\text{ °C}; R_{GS} = 20\text{ k}\Omega$	-	30	V
$V_{GS}$	gate-source voltage		-20	20	V
$I_D$	drain current	$V_{GS} = 10\text{ V}; T_{mb} = 100\text{ °C}$ ; see <a href="#">Figure 1</a>	-	70	A
		$V_{GS} = 10\text{ V}; T_{mb} = 25\text{ °C}$ ; see <a href="#">Figure 1</a>	-	99	A
$I_{DM}$	peak drain current	$t_p \leq 10\text{ }\mu\text{s}$ ; pulsed; $T_{mb} = 25\text{ °C}$ ; see <a href="#">Figure 3</a>	-	396	A
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ °C}$ ; see <a href="#">Figure 2</a>	-	69	W
$T_{stg}$	storage temperature		-55	150	°C
$T_j$	junction temperature		-55	150	°C
<b>Source-drain diode</b>					
$I_S$	source current	$T_{mb} = 25\text{ °C}$	-	99	A
$I_{SM}$	peak source current	$t_p \leq 10\text{ }\mu\text{s}$ ; pulsed; $T_{mb} = 25\text{ °C}$	-	396	A
<b>Avalanche ruggedness</b>					
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$V_{GS} = 10\text{ V}; T_{j(init)} = 25\text{ °C}; I_D = 99\text{ A}; V_{sup} \leq 30\text{ V}; R_{GS} = 50\text{ }\Omega$ ; unclamped	-	41	mJ



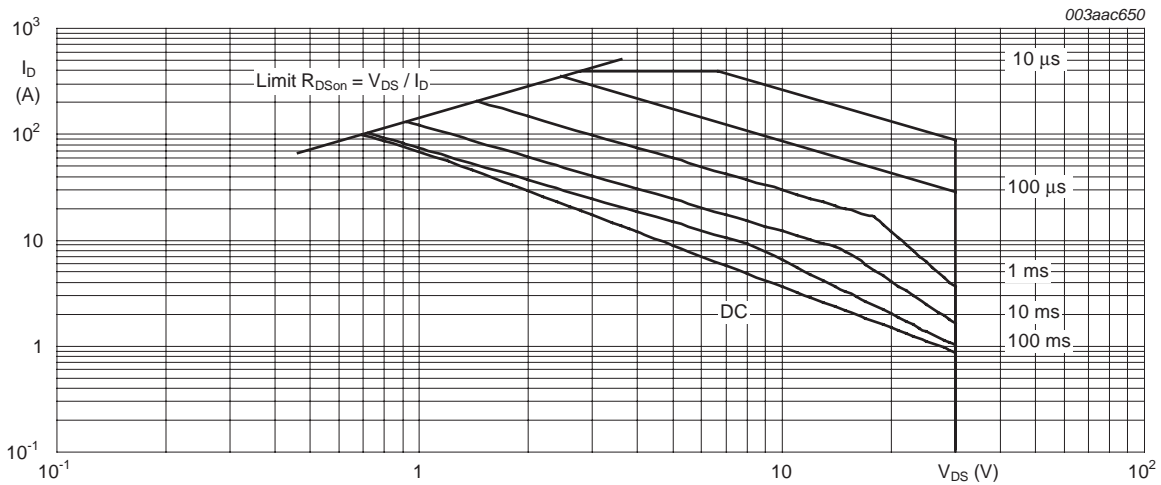
$V_{GS} \geq 10V$

Fig 1. Continuous drain current as a function of mounting base temperature



$$P_{der} = \frac{P_{tot}}{P_{tot(25^\circ C)}} \times 100\%$$

Fig 2. Normalized total power dissipation as a function of mounting base temperature



$T_{mb} = 25^\circ C; I_{DM}$  is single pulse

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

### 5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see <a href="#">Figure 4</a>	-	-	1.82	K/W

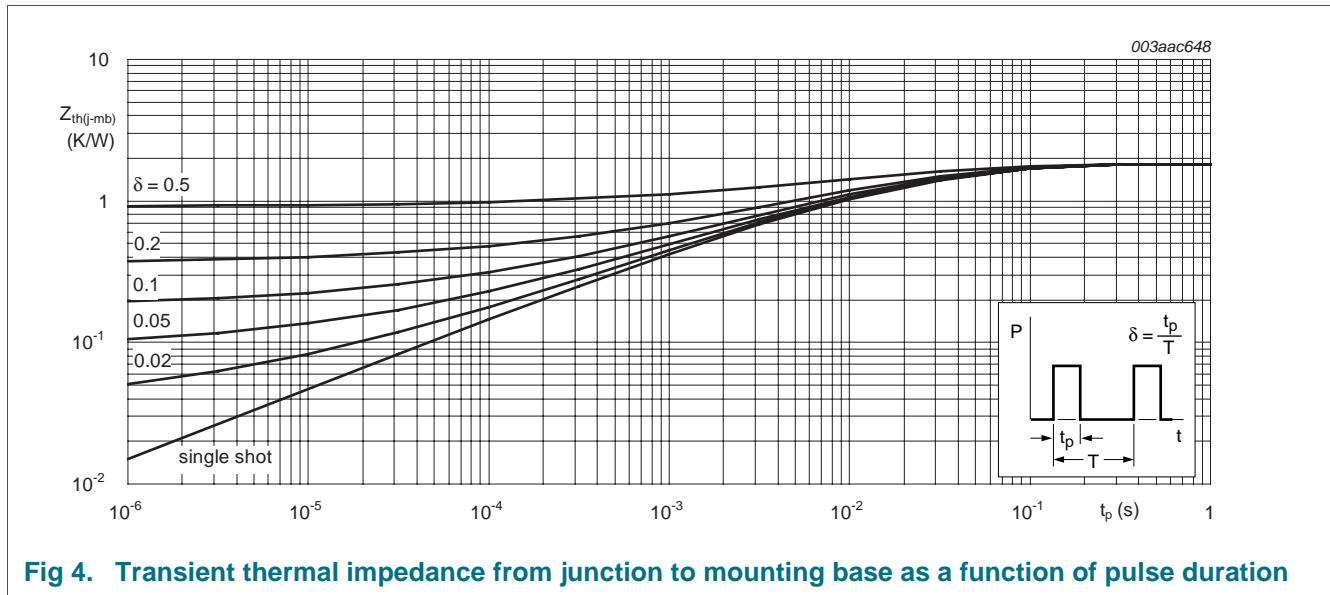


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

## 6. Characteristics

**Table 6. Characteristics**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu\text{A}$ ; $V_{GS} = 0 \text{ V}$ ; $T_j = 25 \text{ }^\circ\text{C}$	30	-	-	V
		$I_D = 250 \mu\text{A}$ ; $V_{GS} = 0 \text{ V}$ ; $T_j = -55 \text{ }^\circ\text{C}$	27	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}$ ; $V_{DS} = V_{GS}$ ; $T_j = 25 \text{ }^\circ\text{C}$ ; see <a href="#">Figure 10</a> ; see <a href="#">Figure 11</a>	1.3	1.7	2.15	V
		$I_D = 1 \text{ mA}$ ; $V_{DS} = V_{GS}$ ; $T_j = 150 \text{ }^\circ\text{C}$ ; see <a href="#">Figure 10</a>	0.65	-	-	V
		$I_D = 1 \text{ mA}$ ; $V_{DS} = V_{GS}$ ; $T_j = -55 \text{ }^\circ\text{C}$ ; see <a href="#">Figure 10</a>	-	-	2.45	V
$I_{DSS}$	drain leakage current	$V_{DS} = 30 \text{ V}$ ; $V_{GS} = 0 \text{ V}$ ; $T_j = 25 \text{ }^\circ\text{C}$	-	-	1	$\mu\text{A}$
		$V_{DS} = 30 \text{ V}$ ; $V_{GS} = 0 \text{ V}$ ; $T_j = 150 \text{ }^\circ\text{C}$	-	-	100	$\mu\text{A}$
$I_{GSS}$	gate leakage current	$V_{GS} = 16 \text{ V}$ ; $V_{DS} = 0 \text{ V}$ ; $T_j = 25 \text{ }^\circ\text{C}$	-	-	100	nA
		$V_{GS} = -16 \text{ V}$ ; $V_{DS} = 0 \text{ V}$ ; $T_j = 25 \text{ }^\circ\text{C}$	-	-	100	nA
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}$ ; $I_D = 15 \text{ A}$ ; $T_j = 25 \text{ }^\circ\text{C}$ ; see <a href="#">Figure 12</a>	-	3.7	6.5	m $\Omega$
		$V_{GS} = 10 \text{ V}$ ; $I_D = 15 \text{ A}$ ; $T_j = 150 \text{ }^\circ\text{C}$ ; see <a href="#">Figure 13</a>	-	-	7	m $\Omega$
		$V_{GS} = 10 \text{ V}$ ; $I_D = 15 \text{ A}$ ; $T_j = 25 \text{ }^\circ\text{C}$ ; see <a href="#">Figure 12</a>	-	2.69	4	m $\Omega$
$R_G$	gate resistance	$f = 1 \text{ MHz}$	-	0.52	-	$\Omega$
<b>Dynamic characteristics</b>						
$Q_{G(tot)}$	total gate charge	$I_D = 10 \text{ A}$ ; $V_{DS} = 12 \text{ V}$ ; $V_{GS} = 10 \text{ V}$ ; see <a href="#">Figure 14</a> ; see <a href="#">Figure 15</a>	-	36.6	-	nC
		$I_D = 10 \text{ A}$ ; $V_{DS} = 12 \text{ V}$ ; $V_{GS} = 4.5 \text{ V}$ ; see <a href="#">Figure 14</a> ; see <a href="#">Figure 15</a>	-	17.6	-	nC
		$I_D = 0 \text{ A}$ ; $V_{DS} = 0 \text{ V}$ ; $V_{GS} = 10 \text{ V}$	-	33	-	nC
$Q_{GS}$	gate-source charge	$I_D = 10 \text{ A}$ ; $V_{DS} = 12 \text{ V}$ ; $V_{GS} = 4.5 \text{ V}$ ; see <a href="#">Figure 14</a> ; see <a href="#">Figure 15</a>	-	5.6	-	nC
$Q_{GD}$	gate-drain charge		-	4.3	-	nC
$Q_{GS(th)}$	pre-threshold gate-source charge		-	3.6	-	nC
$Q_{GS(th-pl)}$	post-threshold gate-source charge		-	2	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	$V_{DS} = 12 \text{ V}$ ; see <a href="#">Figure 14</a> ; see <a href="#">Figure 15</a>	-	2.3	-	V
$C_{iss}$	input capacitance	$V_{DS} = 12 \text{ V}$ ; $V_{GS} = 0 \text{ V}$ ; $f = 1 \text{ MHz}$ ; $T_j = 25 \text{ }^\circ\text{C}$ ; see <a href="#">Figure 16</a>	-	2090	-	pF
$C_{oss}$	output capacitance		-	469	-	pF
$C_{rss}$	reverse transfer capacitance		-	227	-	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 12 \text{ V}$ ; $R_L = 0.5 \text{ } \Omega$ ; $V_{GS} = 4.5 \text{ V}$ ; $R_{G(ext)} = 4.7 \text{ } \Omega$	-	28	-	ns
$t_r$	rise time		-	51	-	ns
$t_{d(off)}$	turn-off delay time		-	44	-	ns
$t_f$	fall time		-	18	-	ns

Table 6. Characteristics ...continued

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Source-drain diode</b>						
$V_{SD}$	source-drain voltage	$I_S = 25\text{ A}$ ; $V_{GS} = 0\text{ V}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; see <a href="#">Figure 17</a>	-	0.88	1.2	V
$t_{rr}$	reverse recovery time	$I_S = 20\text{ A}$ ; $di_S/dt = -100\text{ A/s}$ ; $V_{GS} = 0\text{ V}$ ;	-	39	-	ns
$Q_r$	recovered charge	$V_{DS} = 20\text{ V}$	-	36	-	nC

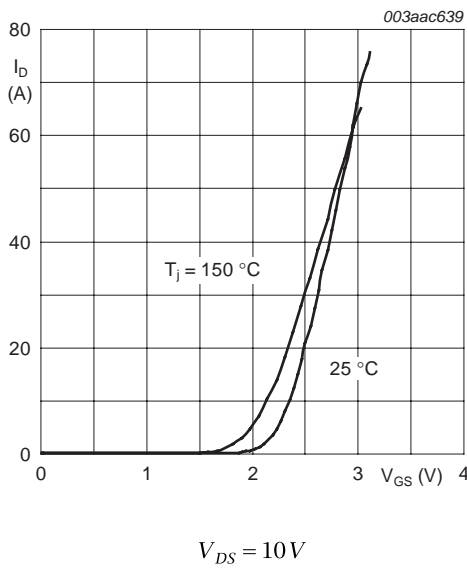


Fig 5. Transfer characteristics: drain current as a function of gate-source voltage; typical values

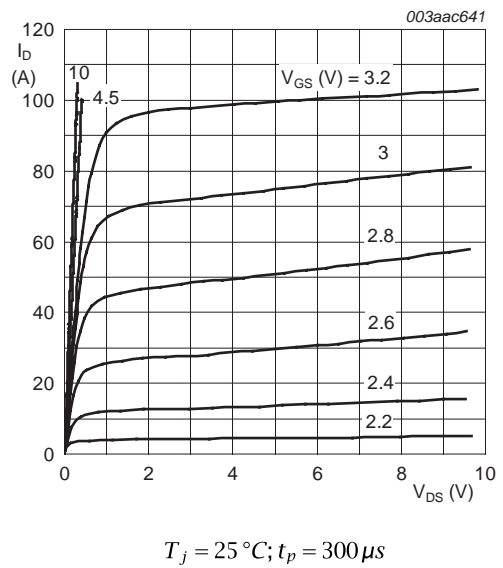


Fig 6. Output characteristics: drain current as a function of drain-source voltage; typical values

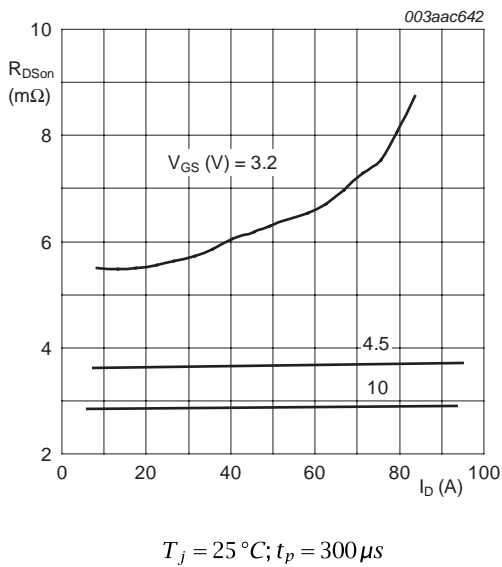


Fig 7. Drain-source on-state resistance as a function of drain current; typical values

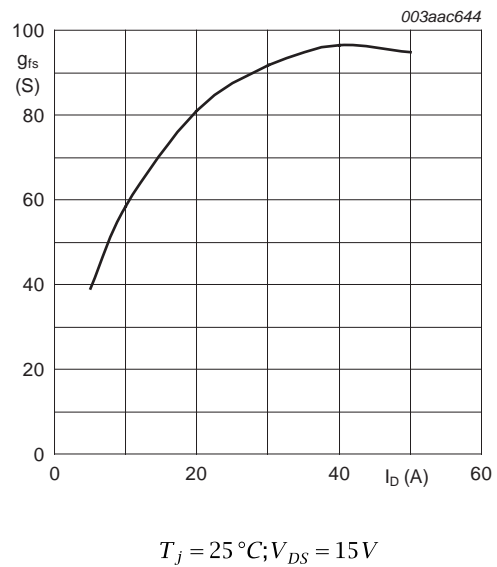
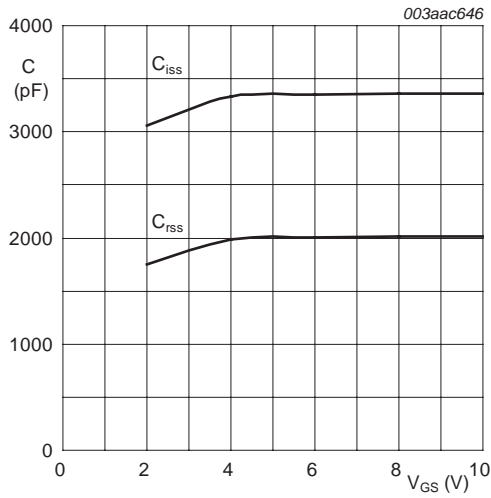
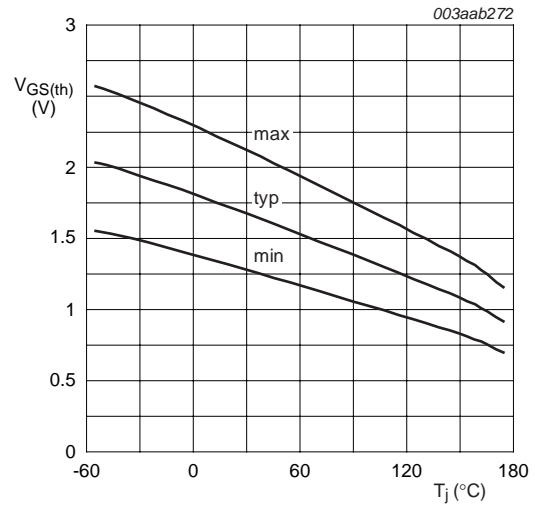


Fig 8. Forward transconductance as a function of drain current; typical values



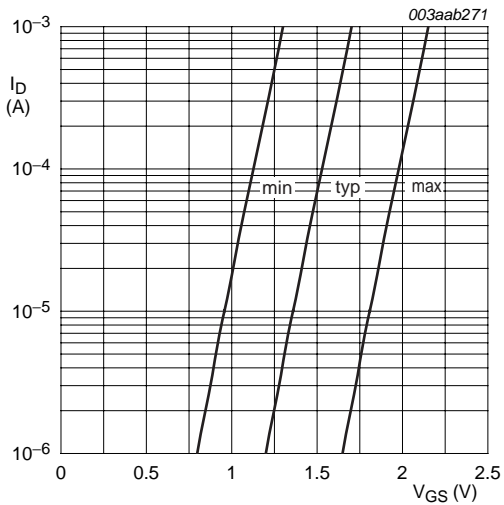
$V_{DS} = 0V; f = 1MHz$

Fig 9. Input and reverse transfer capacitances as a function of gate-source voltage; typical values



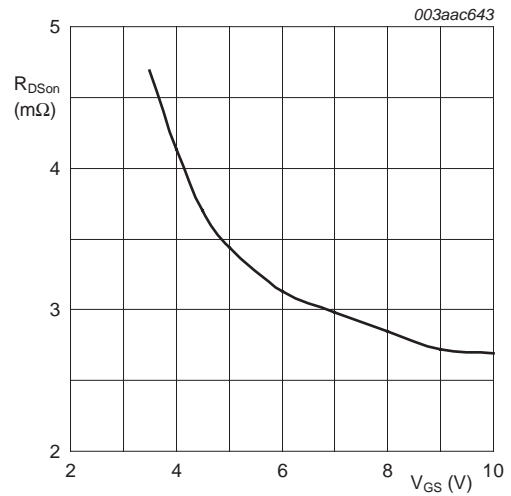
$I_D = 1mA; V_{DS} = V_{GS}$

Fig 10. Gate-source threshold voltage as a function of junction temperature



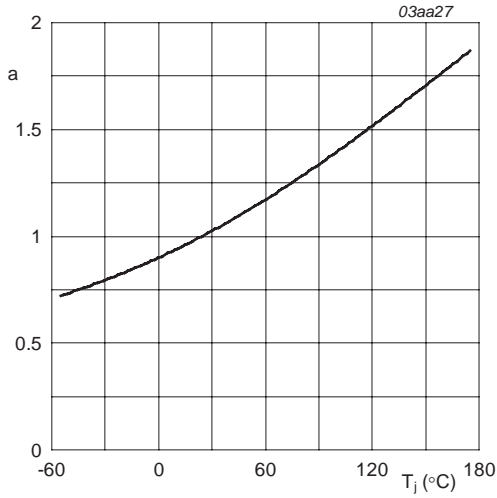
$T_j = 25^\circ C; V_{DS} = 5V$

Fig 11. Sub-threshold drain current as a function of gate-source voltage



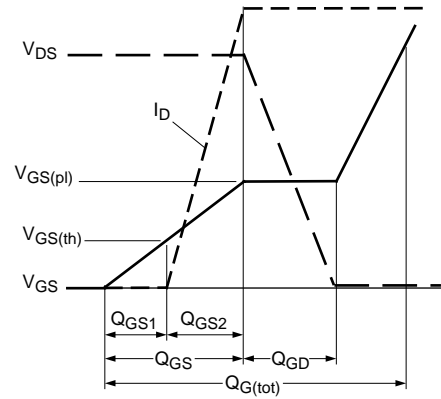
$T_j = 25^\circ C; I_D = 15A$

Fig 12. Drain-source on-state resistance as a function of gate-source voltage; typical values

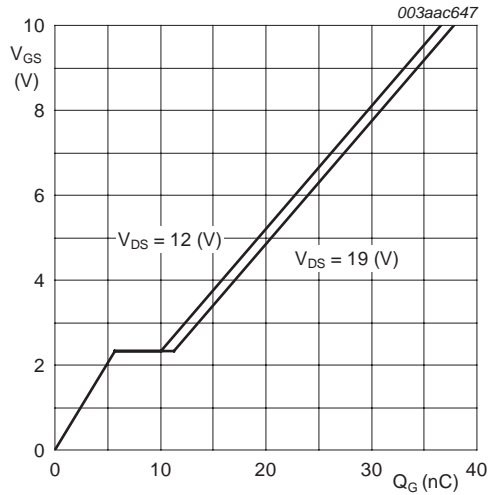


$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

**Fig 13. Normalized drain-source on-state resistance factor as a function of junction temperature**

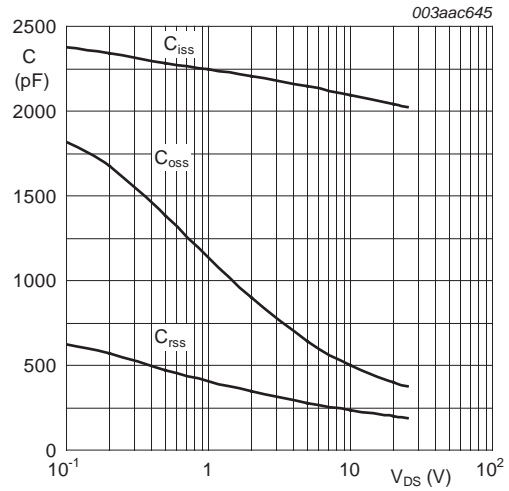


**Fig 14. Gate charge waveform definitions**



$T_j = 25^{\circ}C; I_D = 10A$

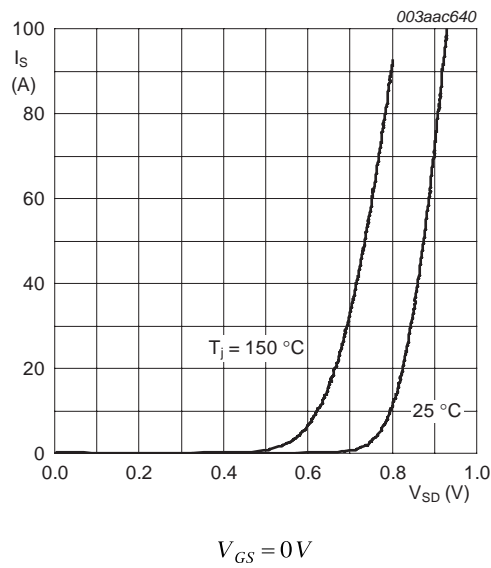
**Fig 15. Gate-source voltage as a function of gate charge; typical values**



$V_{GS} = 0V; f = 1MHz$

**Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values**





**Fig 17. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values**

7. Package outline

Plastic single-ended surface-mounted package (LFAK); 4 leads

SOT669

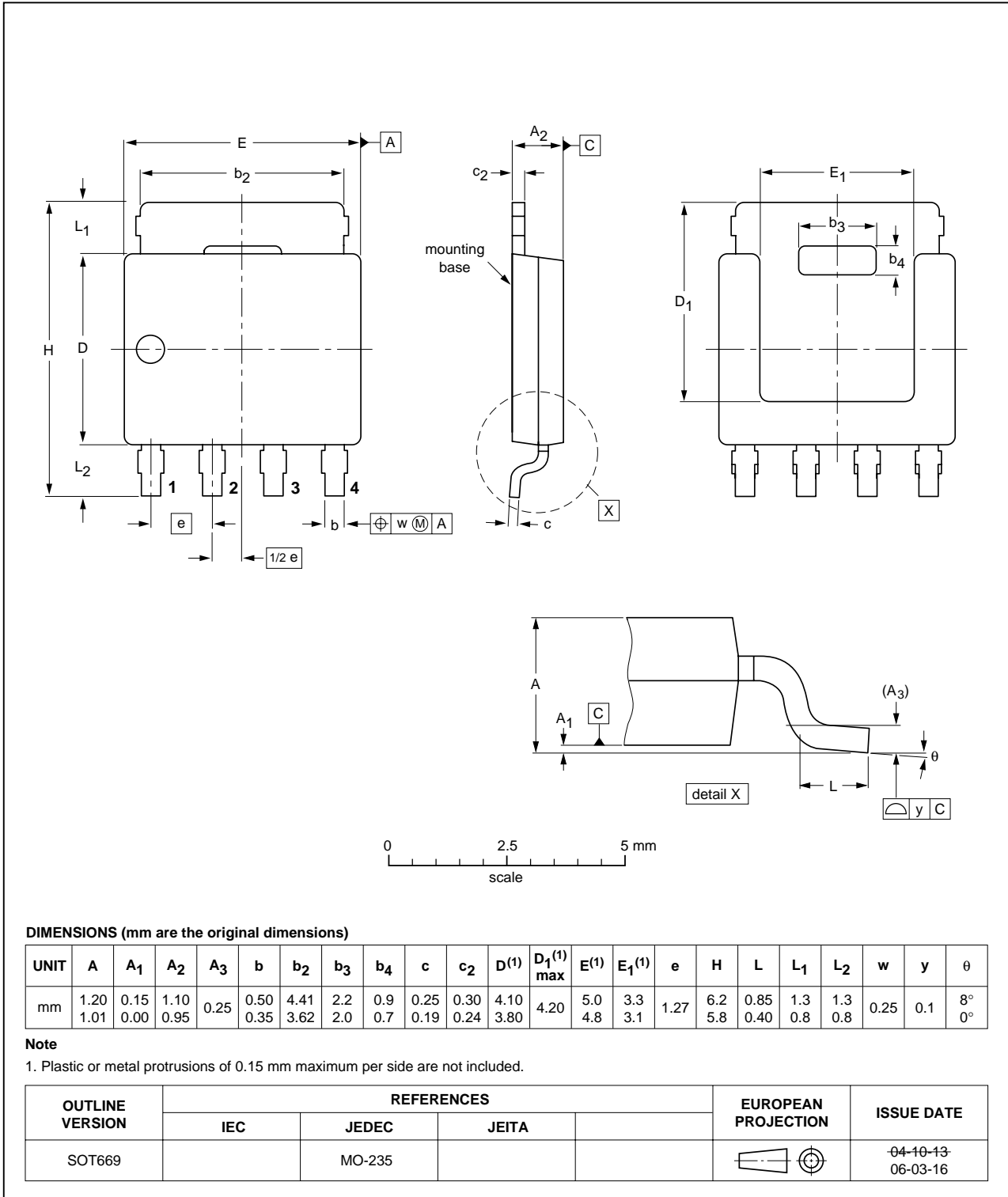


Fig 18. Package outline SOT669 (LFAK)

## 8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN4R0-30YL_1	20080910	Preliminary data sheet	-	-

## 9. Legal information

### 9.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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